



**CHENMKO ENTERPRISE CO.,LTD**

**CHM4308JGP**

**SURFACE MOUNT**

**Dual N-Channel Enhancement Mode Field Effect Transistor**

**VOLTAGE 40 Volts CURRENT 5.8 Ampere**

*Halogens free devices*

**APPLICATION**

- \* Servo motor control.
- \* Power MOSFET gate drivers.
- \* Other switching applications.

**FEATURE**

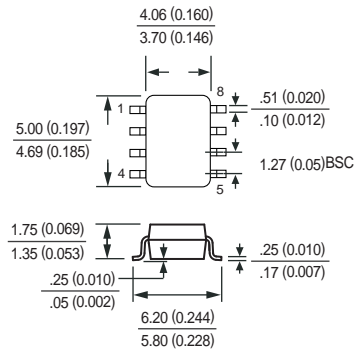
- \* Small flat package. (SO-8 )
- \* High density cell design for extremely low Rds(ON).
- \* Rugged and reliable.
- \* High saturation current capability.

**CONSTRUCTION**

- \* N-Channel Enhancement



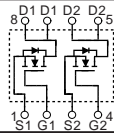
**SO-8**



Dimensions in millimeters

**SO-8**

**CIRCUIT**



**Absolute Maximum Ratings**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	CHM4308JGP	Units
$V_{DSS}$	Drain-Source Voltage	40	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Maximum Drain Current - Continuous	5.8	A
	- Pulsed (Note 3)	23	
$P_D$	Maximum Power Dissipation	2000	mW
$T_J$	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

- Note :
1. Surface Mounted on FR4 Board ,  $t \leq 10\text{sec}$
  2. Pulse Test , Pulse width  $\leq 300\mu\text{s}$  , Duty Cycle  $\leq 2\%$
  3. Repetitive Rating , Pulse width limited by maximum junction temperature
  4. Guaranteed by design , not subject to production trsting

**Thermal characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	62.5	$^\circ\text{C/W}$
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## RATING CHARACTERISTIC CURVES ( CHM4308JGP )

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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### OFF CHARACTERISTICS

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	40			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
$I_{GSSR}$	Gate-Body Leakage	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

### ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1		3	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=5.8\text{A}$		32	38	m $\Omega$
		$V_{GS}=4.5\text{V}, I_D=5.3\text{A}$		40	50	
$g_{FS}$	Forward Transconductance	$V_{DS} = 4.5\text{ V}, I_D = 5.3\text{ A}$		5		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		685		pF
$C_{oss}$	Output Capacitance			115		
$C_{rss}$	Reverse Transfer Capacitance			70		

### SWITCHING CHARACTERISTICS (Note 4)

$Q_g$	Total Gate Charge	$V_{DS}=20\text{V}, I_D=6\text{A}$ $V_{GS}=4.5\text{V}$		6.6	8.7	nC
$Q_{gs}$	Gate-Source Charge			1.9		
$Q_{gd}$	Gate-Drain Charge			3		
$t_{on}$	Turn-On Time	$V_{DD} = 20\text{ V}$ $I_D = 6.0\text{ A}, V_{GS} = 10\text{ V}$ $R_{GEN} = 3\ \Omega$		10	20	nS
$t_r$	Rise Time			4	8	
$t_{off}$	Turn-Off Time			27	54	
$t_f$	Fall Time			4	8	

### DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

$I_S$	Drain-Source Diode Forward Current	(Note 1)			5.8	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$I_S = 1.9\text{ A}, V_{GS} = 0\text{ V}$ (Note 2)			1.3	V